

Supporting Information for

Noncontact Tunneling in Methylammonium Lead Iodide ($\text{CH}_3\text{NH}_3\text{PbI}_3$): Evidence of Bipolar Resistive Switching through Defect Migration

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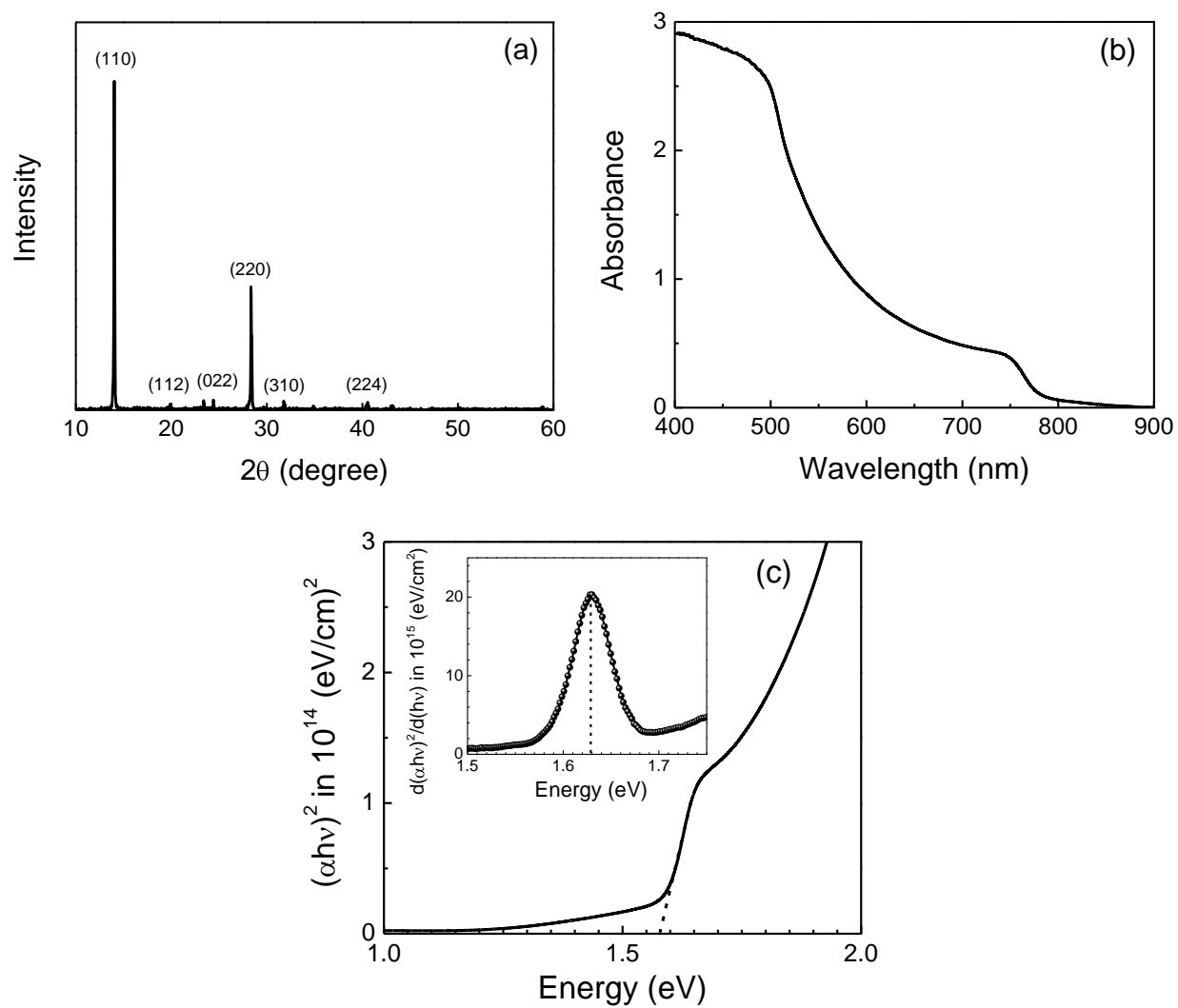


Figure S1. (a) XRD pattern, (b) optical absorption spectrum, and (c) associated Tauc plot along with a plot of $d(\alpha h\nu)^2/d(h\nu)$ versus energy to estimate the optical bandgap of MAPbI₃ perovskite thin-films.

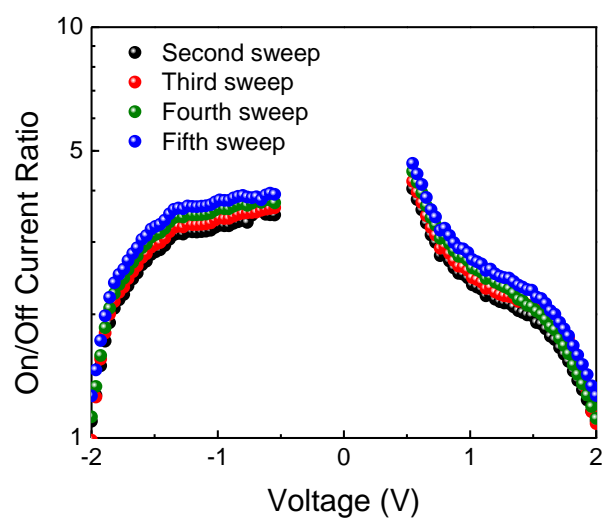


Figure S2. On/Off ratio during subsequent current-voltage scans as mentioned in the legends.

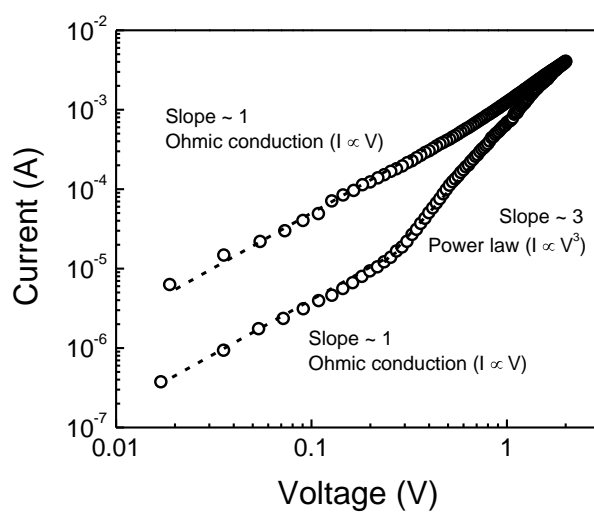


Figure S3. Current-voltage characteristics of a MAPI device in a double-logarithmic scale for the negative voltage region.

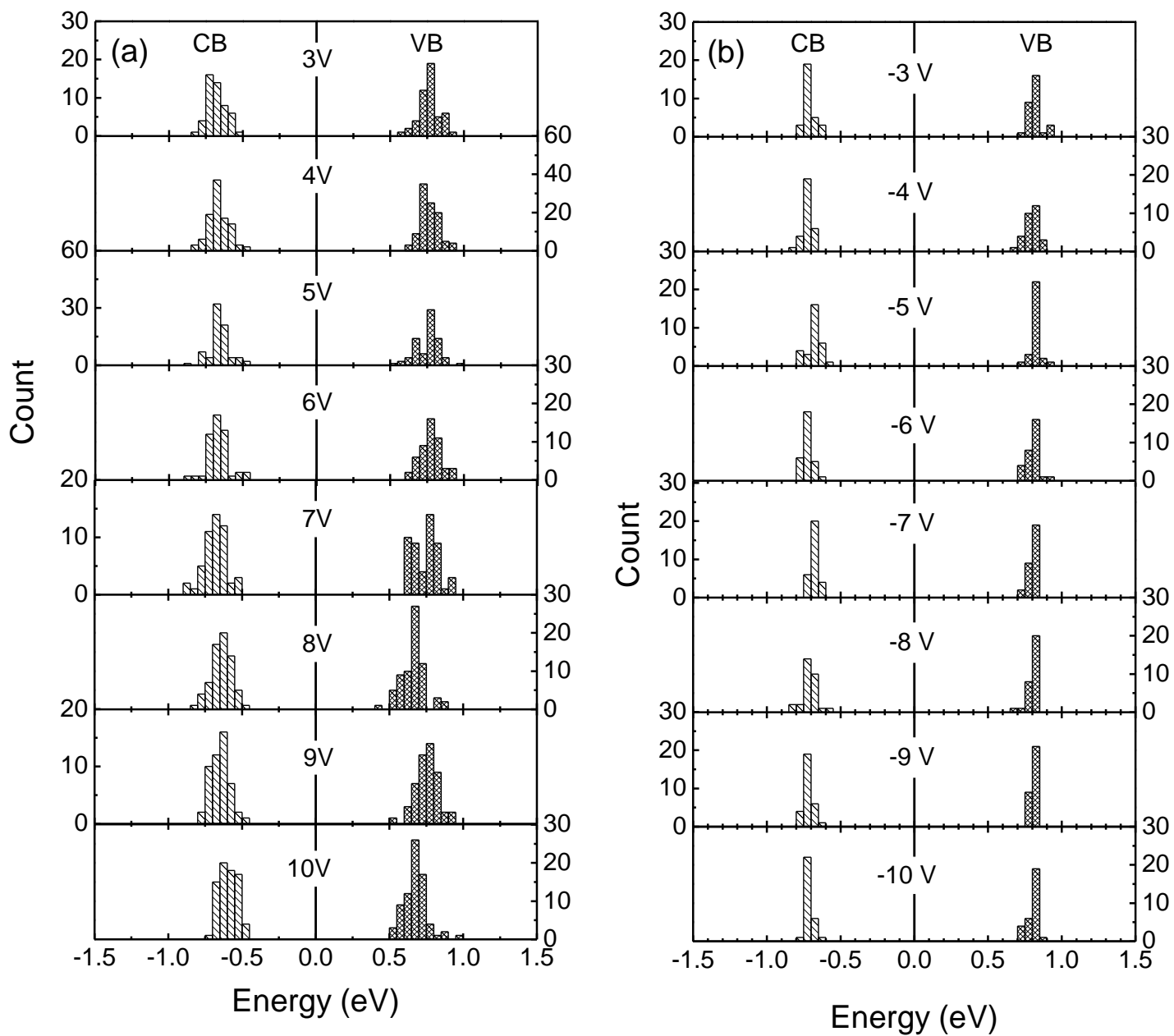


Figure S4. Histograms of band-edges in MAPbI₃ thin-films under (a) positive poling voltages and (b) negative poling voltages as stated in the legends.